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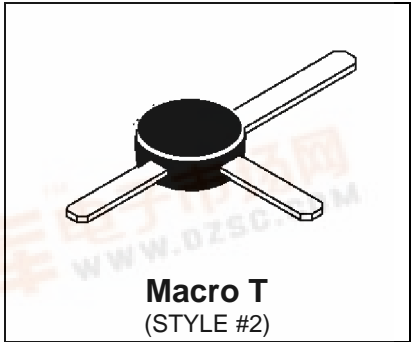
**BFR96**  
**BFR96G**

\* G Denotes RoHS Compliant, Pb Free Terminal Finish

## RF & MICROWAVE DISCRETE LOW POWER TRANSISTORS

### Features

- High Current-Gain – Bandwidth Product,  $fT = 4.5 \text{ GHz (typ) @ } I_C = 50 \text{ mA}$
- Low Noise Figure –  $NF = 2.4 \text{ dB (typ) @ } f = 0.5 \text{ GHz}$
- High Power Gain –  $G_{max} = 14.5\text{dB (typ) @ } f = 0.5 \text{ GHz}$



**DESCRIPTION:** Designed primarily for use in high-gain, low noise, small-signal amplifiers. Also used in applications requiring fast switching times.

### ABSOLUTE MAXIMUM RATINGS (T<sub>case</sub> = 25°C)

Symbol	Parameter	Value	Unit
V <sub>CEO</sub>	Collector-Emitter Voltage	15	Vdc
V <sub>CBO</sub>	Collector-Base Voltage	20	Vdc
V <sub>EBO</sub>	Emitter-Base Voltage	3.0	Vdc
I <sub>C</sub>	Collector Current	100	mA

### Thermal Data

P <sub>D</sub>	Total Device Dissipation @ TC = 100°C	500	mWatts
	Derate above 100°C	10	mW/°C



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ELECTRICAL SPECIFICATIONS (Tcase = 25°C)

STATIC  
(off)

Symbol	Test Conditions	Value			Unit
		Min.	Typ.	Max.	
BVCEO	Collector-Emitter Breakdown Voltage (IC = 1.0 mAdc, IB = 0)	15	-	-	Vdc
BVCB0	Collector-Base Breakdown Voltage (IC = 0.1 mAdc, IE = 0)	20	-	-	Vdc
BVEBO	Emitter-Base Breakdown Voltage (IE = 0.1 mAdc, IC = 0)	3.0	-	-	Vdc
ICBO	Collector Cutoff Current (VCB = 10 Vdc, VBE = 0 Vdc)	-	-	100	nA

(on)

HFE	DC Current Gain (IC = 50 mAdc, VCE = 10 Vdc)	30	-	200	-
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DYNAMIC

Symbol	Test Conditions	Value			Unit
		Min.	Typ.	Max.	
Ftau	Current-Gain – Bandwidth Product (IC = 50 mA, VCE = 10 Vdc, f = 0.5 GHz)	-	5.0	-	GHz
CCB	Output Capacitance (VCB = 10 Vdc, IE = 0, f = 1.0 MHz)	-	2.6	3.2	pF

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FUNCTIONAL

Symbol	Test Conditions	Value			Unit
		Min.	Typ.	Max.	
NF	Noise Figure (IC = 10 mAdc, VCE = 10 Vdc, f = 0.5 GHz)	-	2.0	-	dB
$ S_{21} ^2$	Insertion Gain (IC = 50 mAdc, VCE = 10 Vdc, f = 0.5 GHz)	12	13	-	dB
MSG	Maximum Stable Gain (IC = 50 mAdc, VCE = 10 Vdc, f = 0.5 GHz)	-	16.5	-	dB
$G_{U \max}$	Maximum Unilateral Gain (1) (IC = 50 mAdc, VCE = 10 Vdc, f = 0.5 GHz)	-	14.5	-	dB

**Table 1. Common Emitter S-Parameters, @ VCE = 10 V, IC = 50 mA**

f (MHz)	S11		S21		S12		S22	
	S11	$\angle \phi$	S21	$\angle \phi$	S12	$\angle \phi$	S22	$\angle \phi$
100	0.388	-130	21	112	0.029	66	0.416	-54
200	0.422	-158	11	94	0.046	89	0.277	-71
300	0.432	-168	7.5	86	0.064	72	0.229	-79
500	0.447	178	4.6	75	0.103	75	0.224	-92
700	0.454	170	3.4	65	0.144	74	0.246	-100
800	0.462	167	3	61	0.165	74	0.26	-103
1000	0.479	159	2.5	53	0.212	72	0.284	-112
1500	0.470	138	1.8	32	0.333	66	0.375	-134



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Macro T

Macro X

Power Macro

SO-8

